

# 2SJ547

Silicon P Channel MOS FET  
High Speed Power Switching

# HITACHI

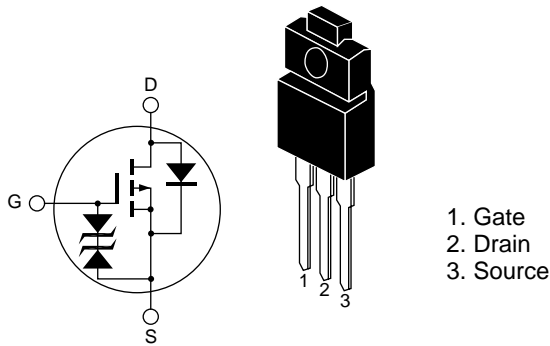
ADE-208-658A (Z)  
2nd. Edition  
Jun 1998

## Features

- Low on-resistance  
 $R_{DS(on)} = 0.16 \Omega$  typ.
- 4 V gate drive devices
- High speed switching

## Outline

TO-220FM



**Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-60	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	-10	A
Drain peak current	I <sub>D(pulse)</sub> <sup>Note1</sup>	-40	A
Body-drain diode reverse drain current	I <sub>DR</sub>	-10	A
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	-10	A
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	8.5	mJ
Channel dissipation	Pch <sup>Note2</sup>	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

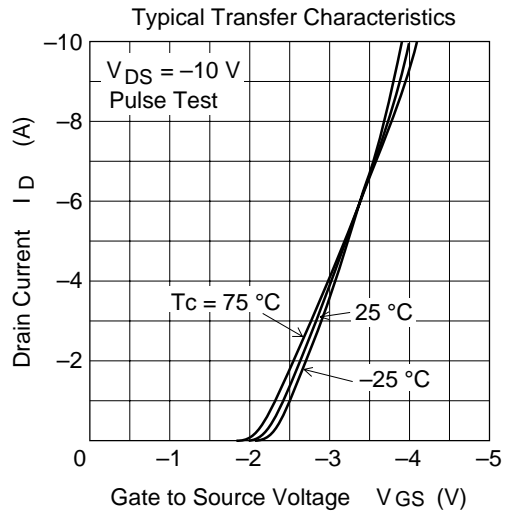
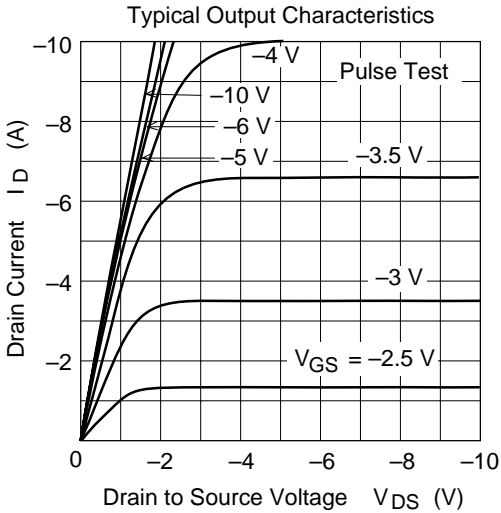
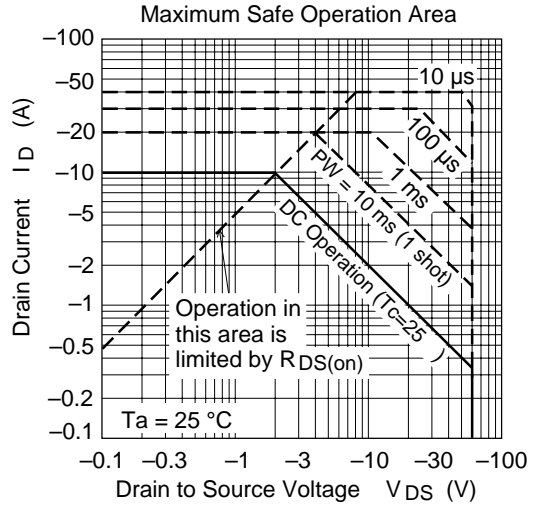
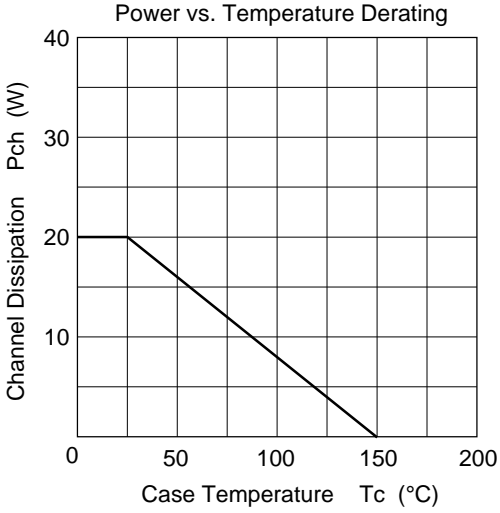
Note: 1. PW ≤ 10μs, duty cycle ≤ 1 %  
 2. Value at Tc = 25°C  
 3. Value at Tch = 25°C, Rg ≥ 50 Ω

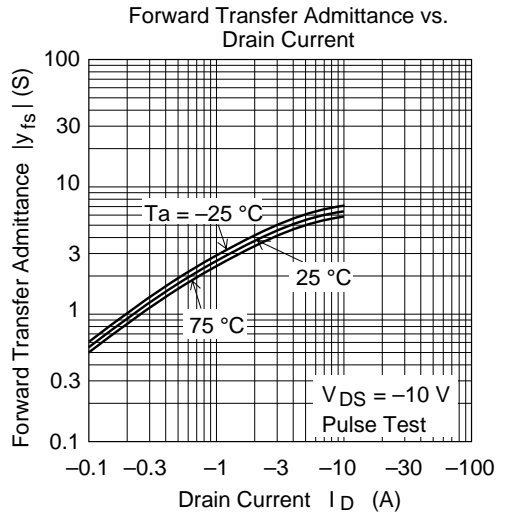
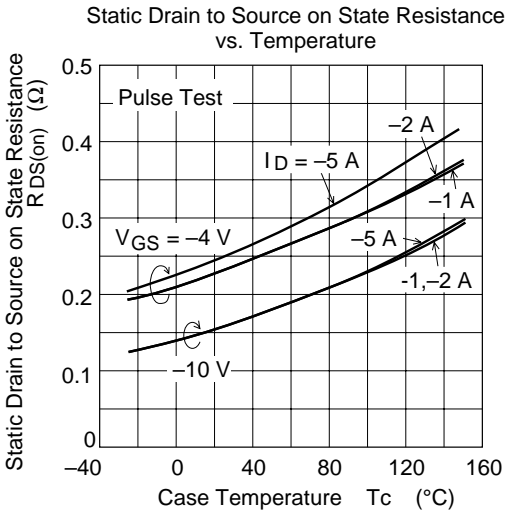
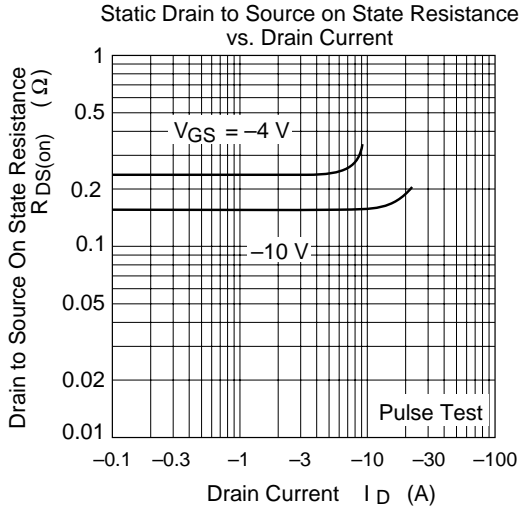
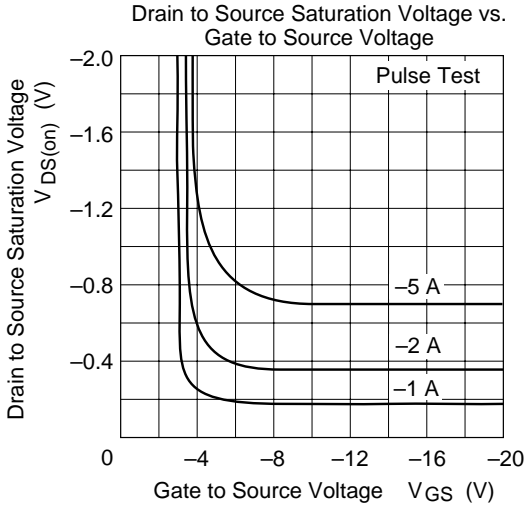
**Electrical Characteristics** (Ta = 25°C)

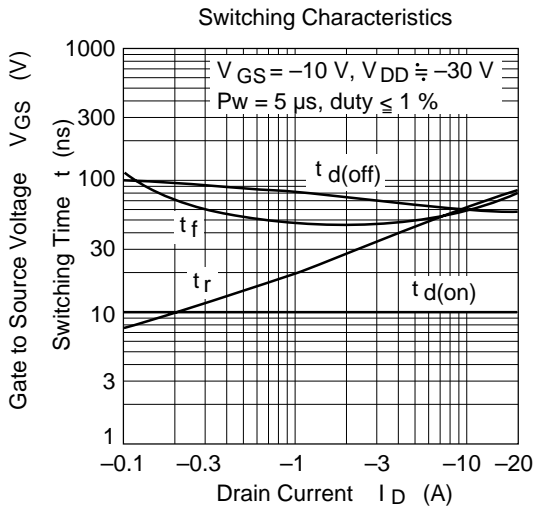
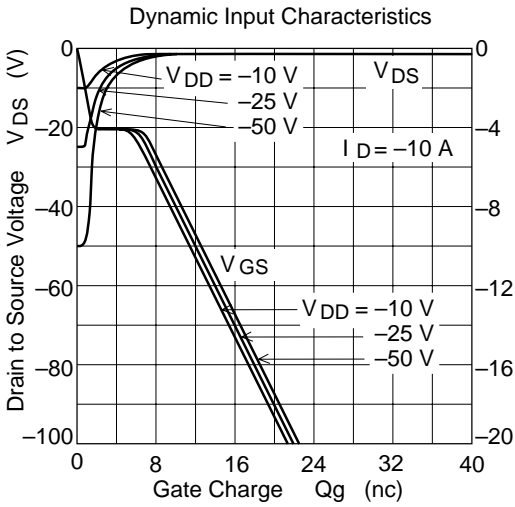
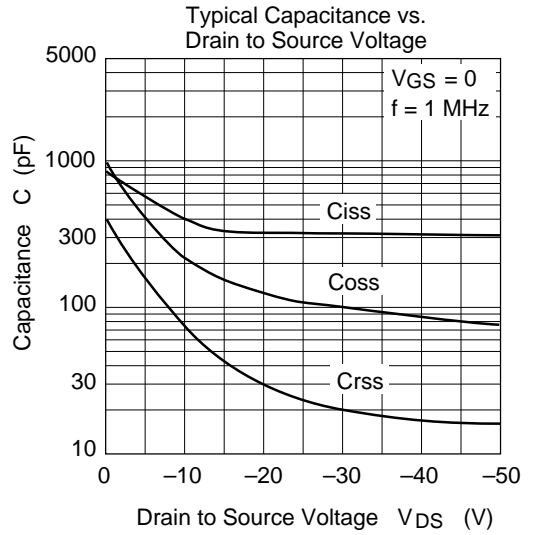
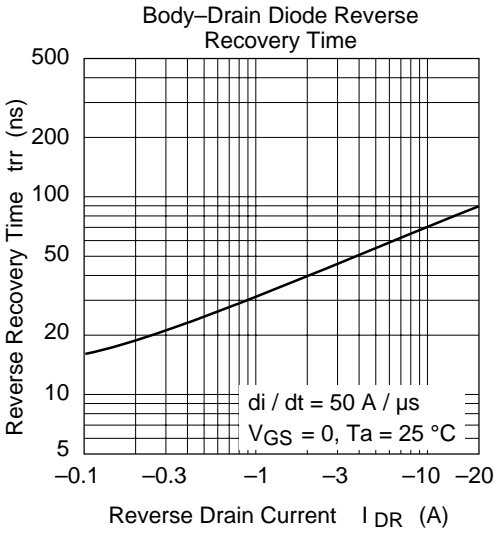
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	-60	—	—	V	I <sub>D</sub> = -10mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100μA, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	-10	μA	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	-1.0	—	-2.0	V	I <sub>D</sub> = -1mA, V <sub>DS</sub> = -10V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	0.16	0.21	Ω	I <sub>D</sub> = -5A, V <sub>GS</sub> = -10V <sup>Note4</sup>
	R <sub>DS(on)</sub>	—	0.23	0.36	Ω	I <sub>D</sub> = -5A, V <sub>GS</sub> = -4V <sup>Note4</sup>
Forward transfer admittance	y <sub>fs</sub>	3.5	5.5	—	S	I <sub>D</sub> = -5A, V <sub>DS</sub> = -10V <sup>Note4</sup>
Input capacitance	Ciss	—	400	—	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	—	220	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	Crss	—	75	—	pF	f = 1MHz
Turn-on delay time	t <sub>d(on)</sub>	—	10	—	ns	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A
Rise time	t <sub>r</sub>	—	45	—	ns	R <sub>L</sub> = 6Ω
Turn-off delay time	t <sub>d(off)</sub>	—	65	—	ns	
Fall time	t <sub>f</sub>	—	50	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	-1.2	—	V	I <sub>F</sub> = -10A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	70	—	ns	I <sub>F</sub> = -10A, V <sub>GS</sub> = 0 dI <sub>F</sub> /dt = 50A/μs

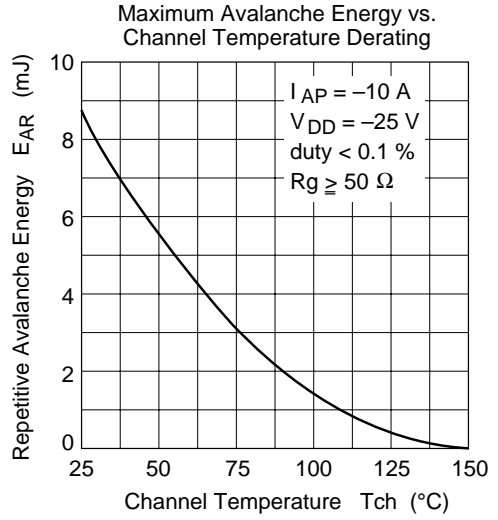
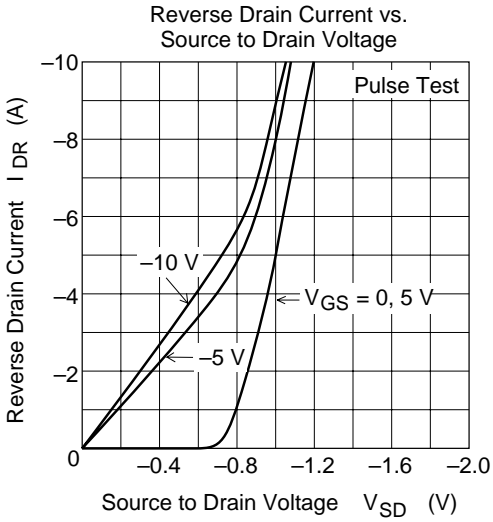
Note: 4. Pulse test

Main Characteristics

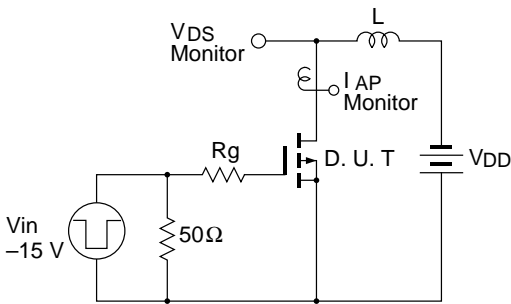




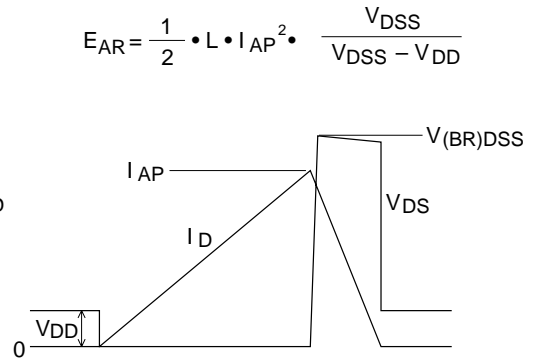




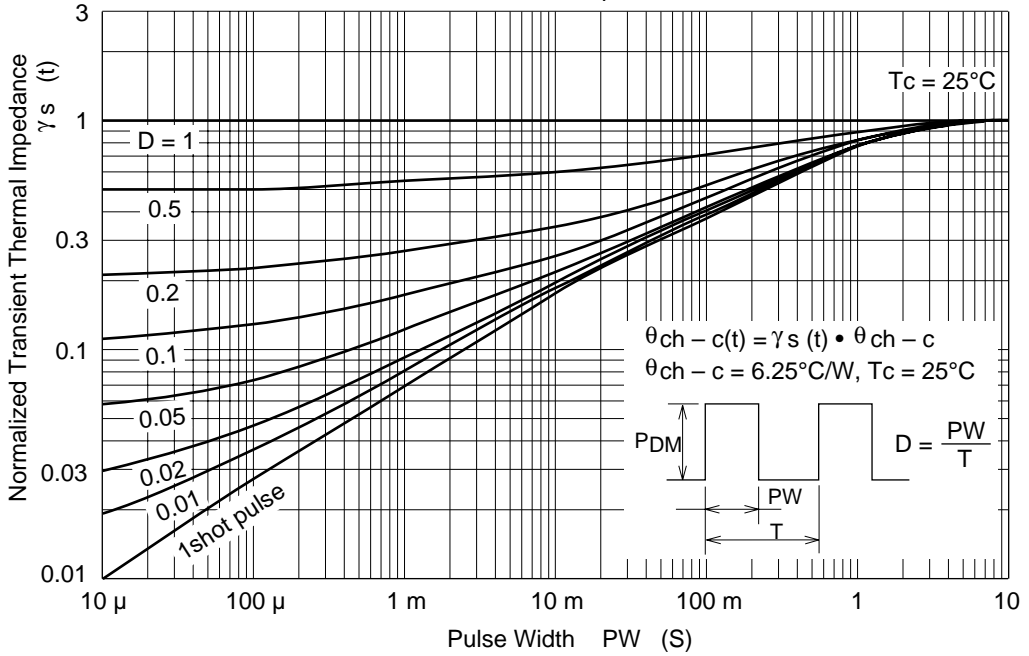
Avalanche Test Circuit



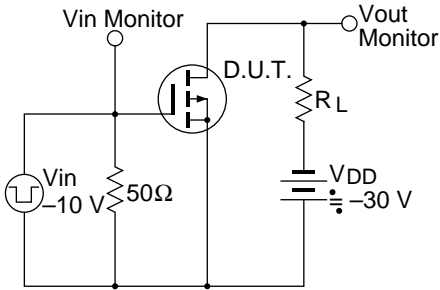
Avalanche Waveform



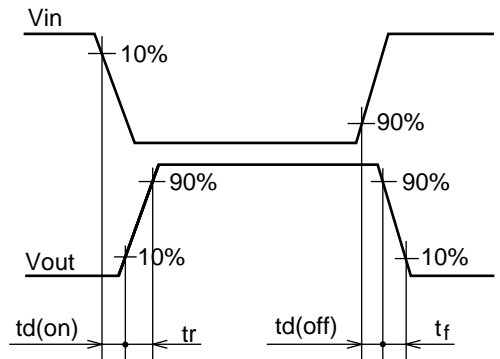
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit

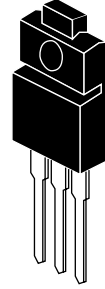
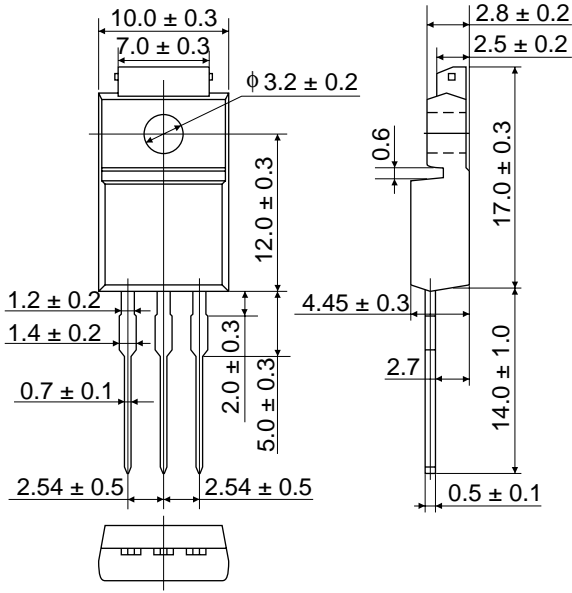


Waveform



Package Dimensions

Unit: mm



Hitachi Code	TO-220FM
EIAJ	SC-72
JEDEC	—



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